





P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _A = +25°C
201/	$65m\Omega$ @ $V_{GS} = -10V$	-3.9A
-30V	99mΩ @ V _{GS} = -4.5V	-3.2A

Description

This MOSFET has been designed to minimize the on-state resistance $(R_{DS(ON)})$ yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen- and Antimony-Free. "Green" Device (Note 3)
- The DMP3097LQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

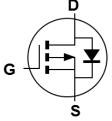
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish—Matte Tin Annealed over Copper Lead-Frame.
 Solderable per MIL-STD-202, Method 208 ©3
- Terminal Connections: See Diagram
- Weight: 0.008 grams (Approximate)

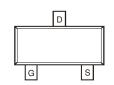




Top View



Equivalent Circuit



Top View Pin Configuration

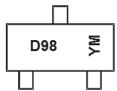
Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3097LQ-7	SOT23	3000/Tape & Reel
DMP3097LQ-13	SOT23	10000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



D98= Product Type Marking Code YM = Date Code Marking Y = Year (ex: H = 2020)

M = Month (ex: 9 = September)

Year	2020	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031
Code	Н		J	K	L	М	N	0	Р	R	S	T
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
								_	_	_	N	_



Maximum Ratings (@ T_A = +25°C, unless otherwise specified.)

Characterist	tic		Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	±20	V
Drain Current (Note 6) $V_{GS} = -10V$ Steady $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$			<u> </u>	-3.9 -3.1	А
Pulsed Drain Current (10µs Pulse, Duty	Cycle = 1%)		I _{DM}	-20	Α

Thermal Characteristics

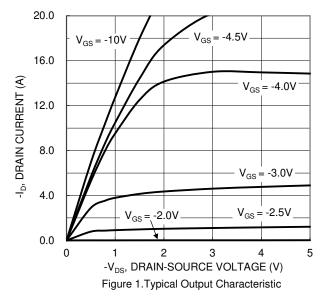
Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	P_{D}	1.0	W
Thermal Resistance, Junction to Ambient @ T _A = +25°C (Note 5)	R _{0JA}	123	°C/W
Total Power Dissipation (Note 6)	P_D	1.52	W
Thermal Resistance, Junction to Ambient @ T _A = +25°C (Note 6)	$R_{\theta JA}$	82	°C/W
Operating and Storage Temperature Range	$T_{J_1}T_{STG}$	-55 to +150	°C

Electrical Characteristics (@ T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS (Note 7)								
Drain-Source Breakdown Voltage	BV _{DSS}	-30	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$		
Zero Gate Voltage Drain Current	I _{DSS}	ı	_	-800	nA	$V_{DS} = -30V, V_{GS} = 0V$		
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$		
ON CHARACTERISTICS (Note 7)	ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	-1.0	_	-2.1	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$		
Static Drain-Source On-Resistance	D		53	65	mΩ	$V_{GS} = -10V, I_D = -3.8A$		
Static Dialii-Source Oil-nesistance	R _{DS(ON)}		74	99	11122	$V_{GS} = -4.5V, I_D = -3.0A$		
Diode Forward Voltage (Note 6)	V _{SD}	1	-0.85	-1.26	V	$V_{GS} = 0V$, $I_{S} = -2.7A$		
DYNAMIC CHARACTERISTICS (Note 8)								
Input Capacitance	C _{iss}	1	563	_	pF	V 05V V 0V		
Output Capacitance	Coss	I	48		pF	$V_{DS} = -25V, V_{GS} = 0V,$ f = 1.0MHz		
Reverse Transfer Capacitance	Crss	I	41		pF			
Gate Resistance	R _G	1	9.5	_	Ω	$V_{GS} = 0V$, $V_{DS} = 0V$, $f = 1MHz$		
Total Gate Charge	Qa	_	6.6	_		$V_{DS} = -15V, V_{GS} = -4.5V,$ $I_{D} = -3.8A$		
		_	13.4	_	nC			
Gate-Source Charge	Qgs	1	2.5	_		$V_{DS} = -15V$, $V_{GS} = -10V$, $I_{D} = -3.8A$		
Gate-Drain Charge	Q_{gd}	_	1.5	_				
Turn-On Delay Time	t _{D(ON)}	_	10	_				
Turn-On Rise Time	t _R	_	2.3	_	ns	$V_{DS} = -15V, V_{GS} = -10V,$		
Turn-Off Delay Time	t _{D(OFF)}		31	_		$I_D = -1A$, $R_G = 6.0\Omega$		
Turn-Off Fall Time	t _F		11	_				

 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.
 Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing. Notes:





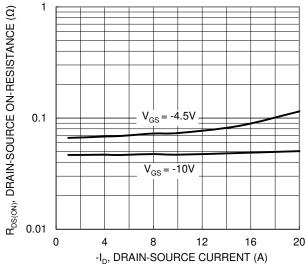


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

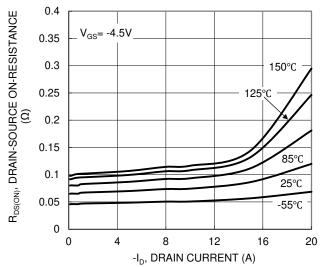


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

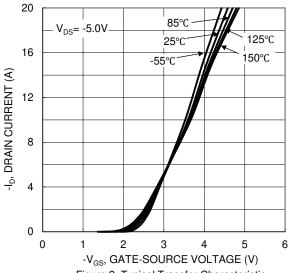


Figure 2. Typical Transfer Characteristic

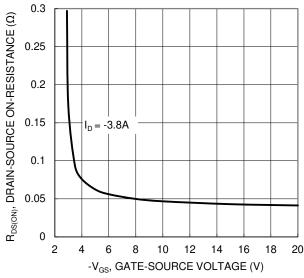


Figure 4. Typical Transfer Characteristic

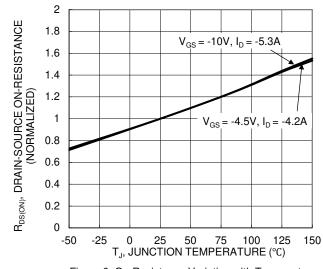


Figure 6. On-Resistance Variation with Temperature



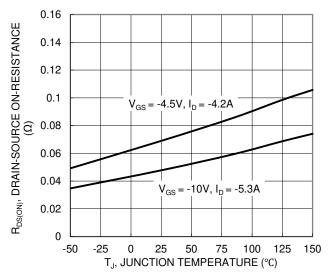


Figure 7. On-Resistance Variation with Temperature

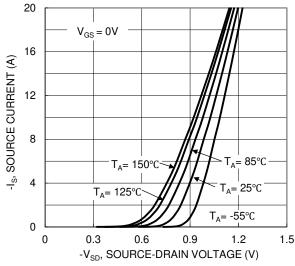


Figure 9. Diode Forward Voltage vs. Current

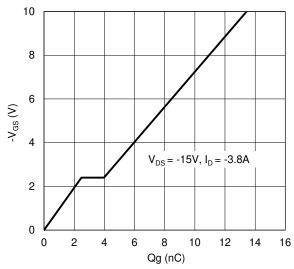


Figure 11. Gate Charge

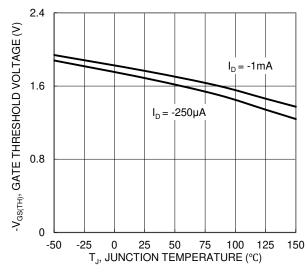


Figure 8. Gate Threshold Variation vs. JunctionTemperature

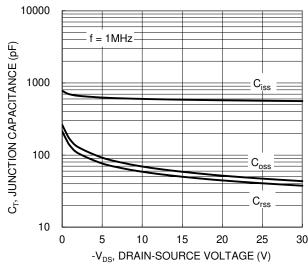


Figure 10. Typical Junction Capacitance

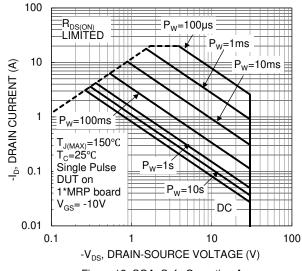


Figure 12. SOA, Safe Operation Area

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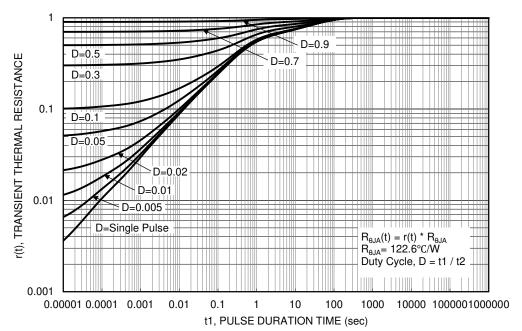


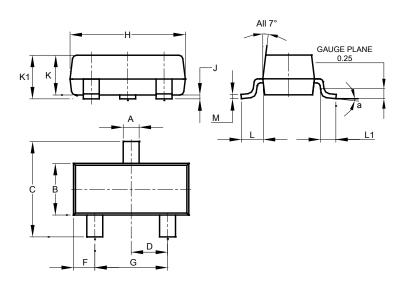
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23

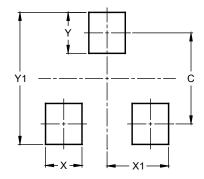


	SOT23							
Dim	Min	Max	Тур					
Α	0.37	0.51	0.40					
В	1.20	1.40	1.30					
С	2.30	2.50	2.40					
D	0.89	1.03	0.915					
F	0.45	0.60	0.535					
G	1.78	2.05	1.83					
Н	2.80	3.00	2.90					
J	0.013	0.10	0.05					
K	0.890	1.00	0.975					
K1	0.903	1.10	1.025					
L	0.45	0.61	0.55					
L1	0.25	0.55	0.40					
М	0.085	0.150	0.110					
а	0°	8°						
All Dimensions in mm								

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT23



Dimensions	Value (in mm)				
С	2.0				
Х	0.8				
X1	1.35				
Υ	0.9				
Y1	2.9				



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